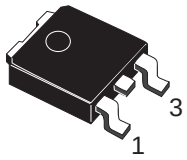
STGD7NB60S

N-CHANNEL 7A - 600V DPAK
Power MESH™ IGBT

TYPE	V_{CES}	$V_{CE(sat)}$	I_C
STGD7NB60S	600 V	< 1.6 V	7 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- VERY LOW ON-VOLTAGE DROP (V_{cesat})
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")



DPAK
TO-252
(Suffix "T4")

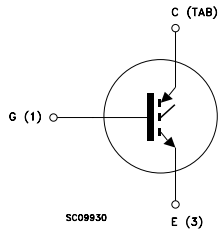
DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding perfomances. The suffix "S" identifies a family optimized to achieve minimum on-voltage drop for low frequency applications (<1kHz).

APPLICATIONS

- LIGHT DIMMER
- STATIC RELAYS
- MOTOR CONTROL

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage (V_{GS} = 0)	600	V
V_{ECR}	Reverse Battery Protection	20	V
V_{GE}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current (continuous) at T_c = 25 °C	15	A
I_C	Collector Current (continuous) at T_c = 100 °C	7	A
I_{CM}(•)	Collector Current (pulsed)	60	A
P_{tot}	Total Dissipation at T_c = 25 °C	55	W
	Derating Factor	0.44	W/°C
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	2.27	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	100	°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	1.5	°C/W

ELECTRICAL CHARACTERISTICS (T_j = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	I_C = 250 µA V_{GE} = 0	600			V
$V_{BR(ECR)}$	Emitter-Collector Breakdown Voltage	IC = 1 mA V_{GE} = 0	20			V
I_{CES}	Collector cut-off (V_{GE} = 0)	V_{CE} = Max Rating T_j = 25 °C V_{CE} = Max Rating T_j = 125 °C			10 100	µA µA
I_{GES}	Gate-Emitter Leakage Current (V_{CE} = 0)	V_{GE} = ± 20 V V_{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	V_{CE} = V_{GE} I_C = 250 µA	2.5		5	V
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	V_{GE} = 15 V I_C = 3 A V_{GE} = 15 V I_C = 7 A V_{GE} = 15 V I_C = 7 A T_j = 125 °C		1 1.2 1.1	1.4 1.6	V V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	V_{CE} =25 V I_C = 7 A	4			S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{CE} = 25 V f = 1 MHz V_{GE} = 0		610 65 12	780 85 15	pF pF pF
Q_G	Gate Charge	V_{CE} = 400 V I_C = 7 A V_{GE} = 15 V		33		nC
I_{CL}	Latching Current	V_{clamp} = 480 V R_G=1kΩ T_j = 150 °C	15			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Delay Time Rise Time	V_{CC} = 480 V I_C = 7 A V_{GE}= 15 V R_G = 1 KΩ		0.7 0.46		µs µs
$(di/dt)_{on}$	Turn-on Current Slope	V_{CC} = 480 V I_C = 7 A R_G = 1 KΩ V_{GE} = 15 V		8		A/µs
E_{on}	Turn-on Switching Losses	T_j = 125 °C		0.4		mJ

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING OFF

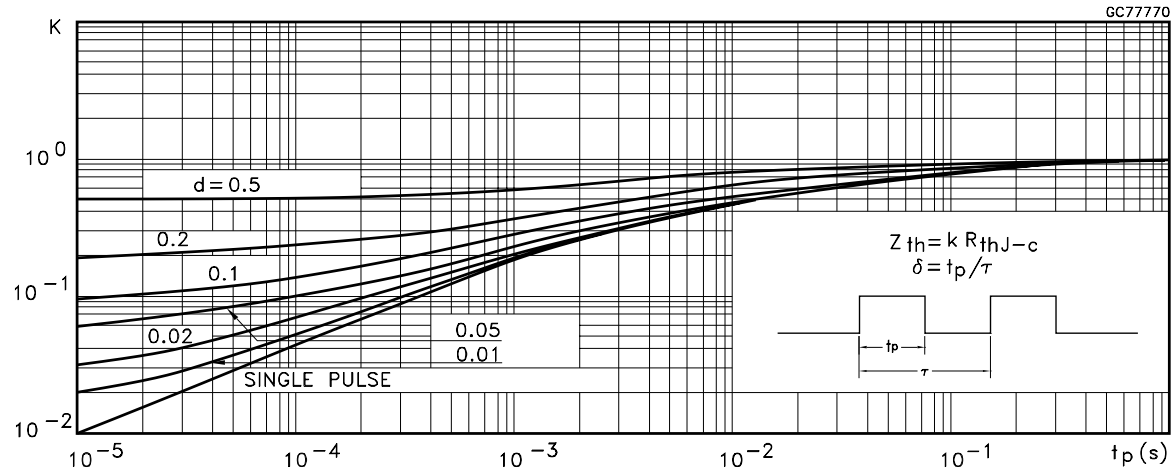
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t_c	Cross-Over Time	V_{CC} = 480 V	I_C = 7 A		2.2		µs
$t_r(v_{off})$	Off Voltage Rise Time	R_{GE} = 100 Ω	V_{GE} = 15 V		1.2		µs
t_f	Fall Time				1.2		µs
E_{off}(**)	Turn-off Switching Loss				3.5		mJ
t_c	Cross-Over Time	V_{CC} = 480 V	I_C = 7 A		3.8		µs
$t_r(v_{off})$	Off Voltage Rise Time	R_{GE} = 100 Ω	V_{GE} = 15 V		1.2		µs
t_f	Fall Time	T_j = 125 °C			1.9		µs
E_{off}(**)	Turn-off Switching Loss				5.3		mJ

(•) Pulse width limited by safe operating area

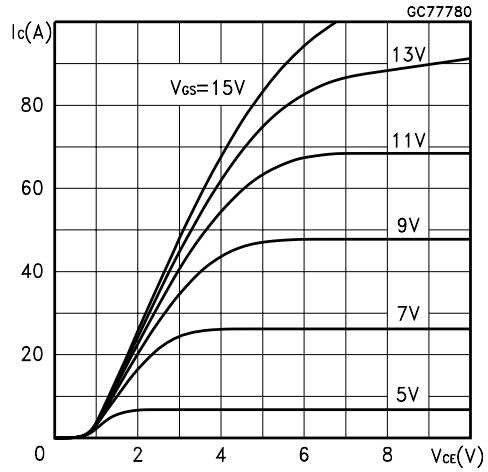
(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(**)Losses Include Also The Tail (Jedec Standardization)

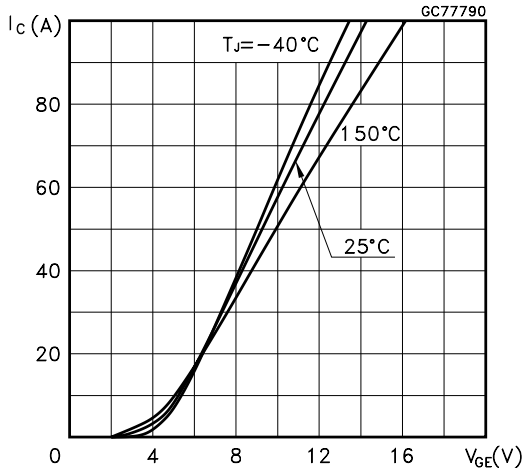
Thermal Impedance



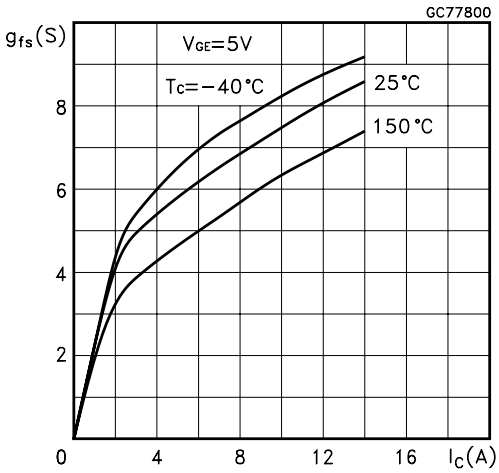
Output Characteristics



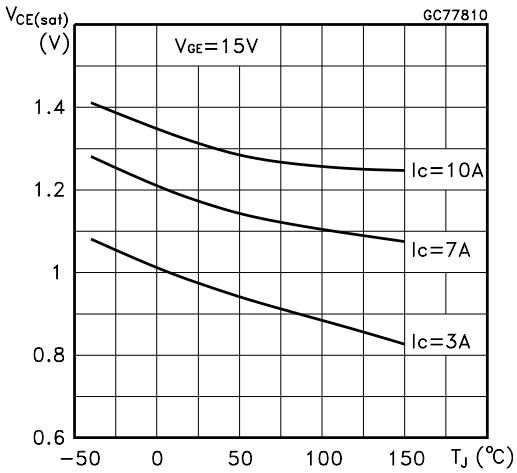
Transfer Characteristics



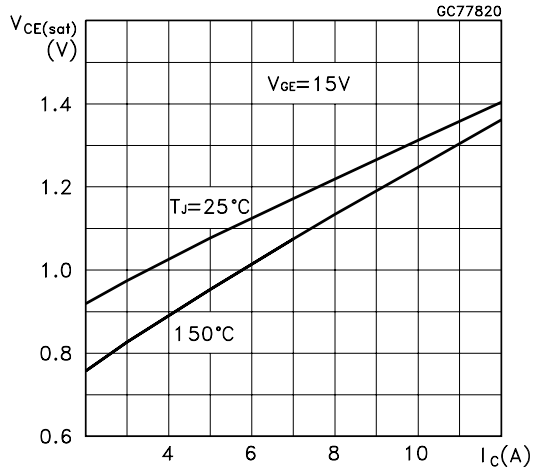
Transconductance



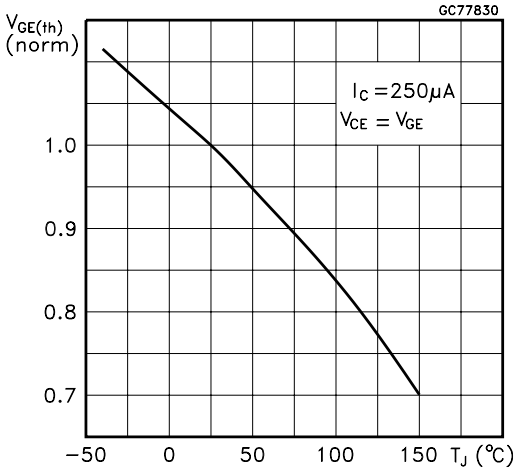
Collector-Emitter On Voltage vs Temperature



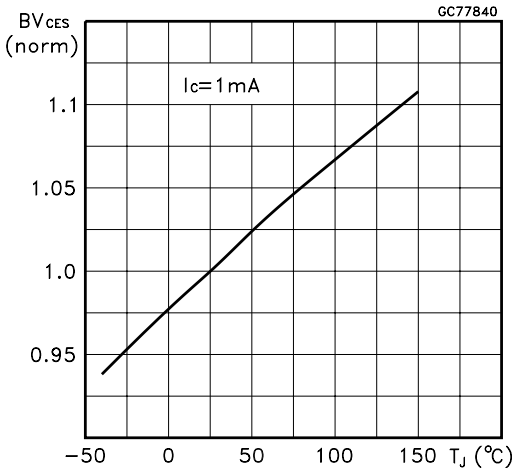
Collector-Emitter On Voltage vs Collector Current



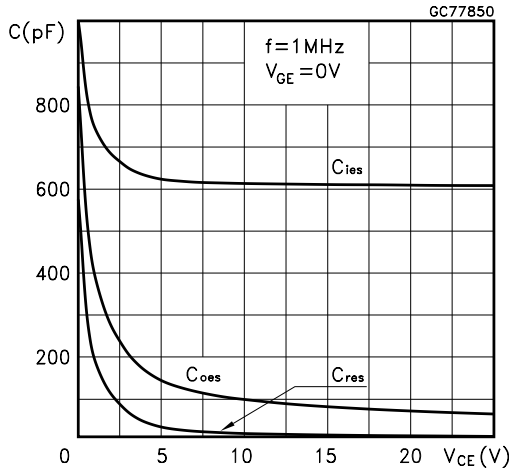
Gate Threshold vs Temperature



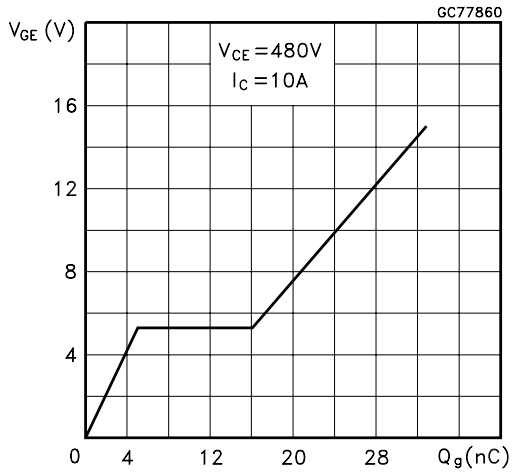
Normalized Breakdown Voltage vs Temperature



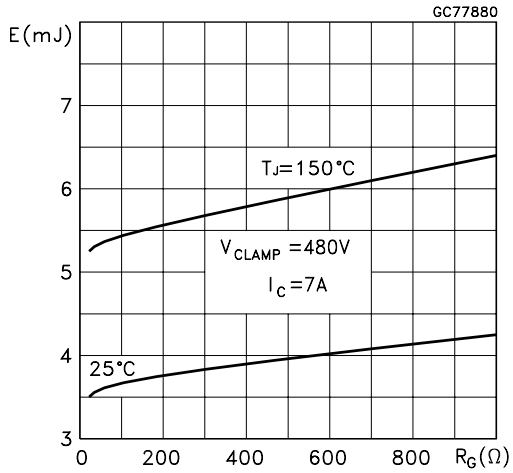
Capacitance Variations



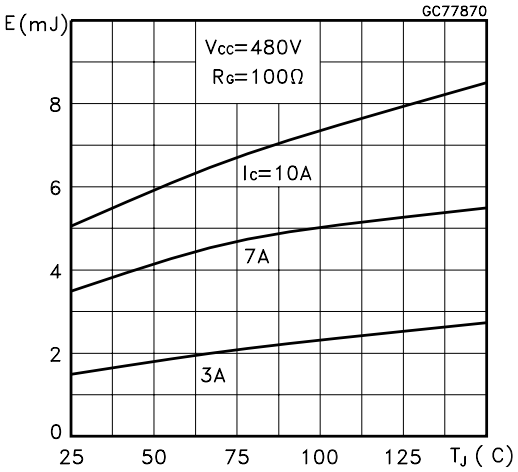
Gate Charge vs Gate-Emitter Voltage



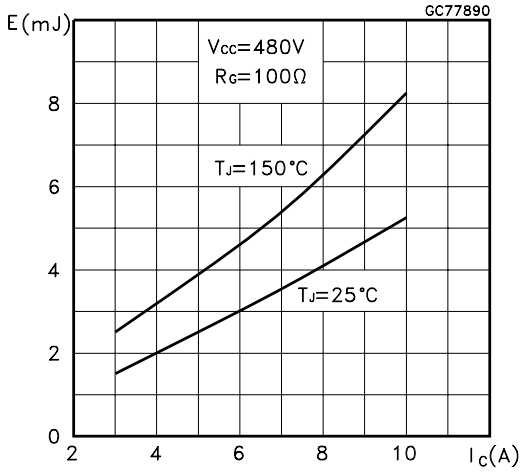
Off Losses vs Gate Resistance



Off Losses vs Temperature



Off Losses vs Collector Current



Switching Off Safe Operatin Area

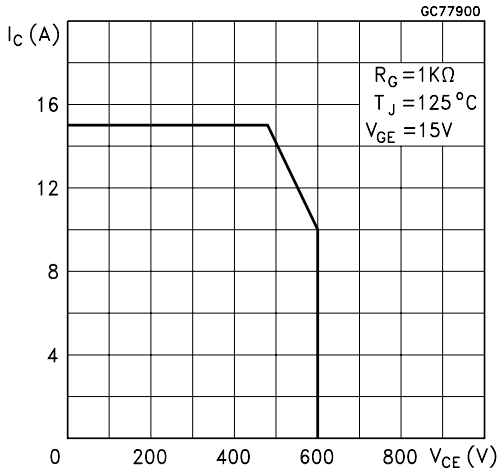
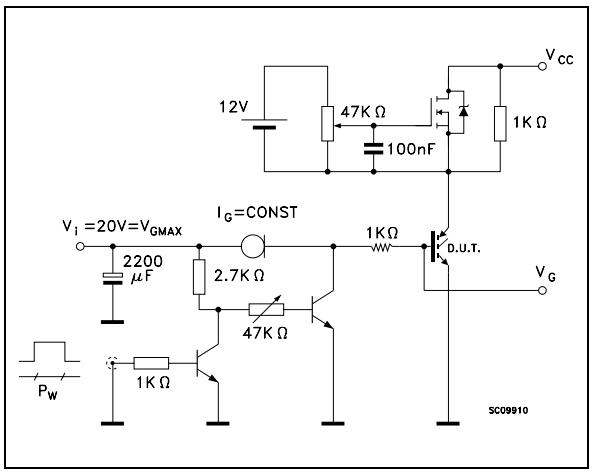


Fig. 1: Gate Charge test Circuit

Fig. 2: Test Circuit For Inductive Load Switching



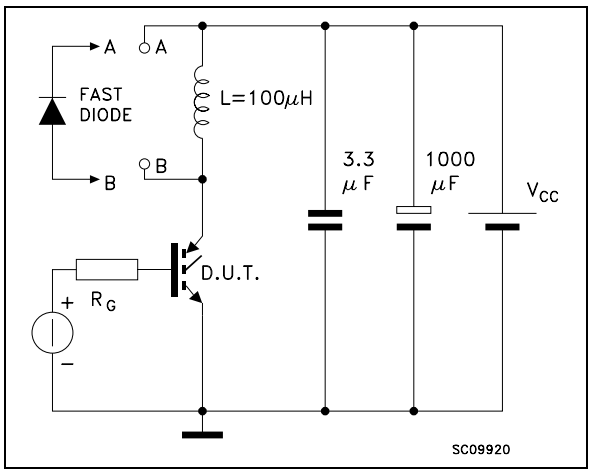
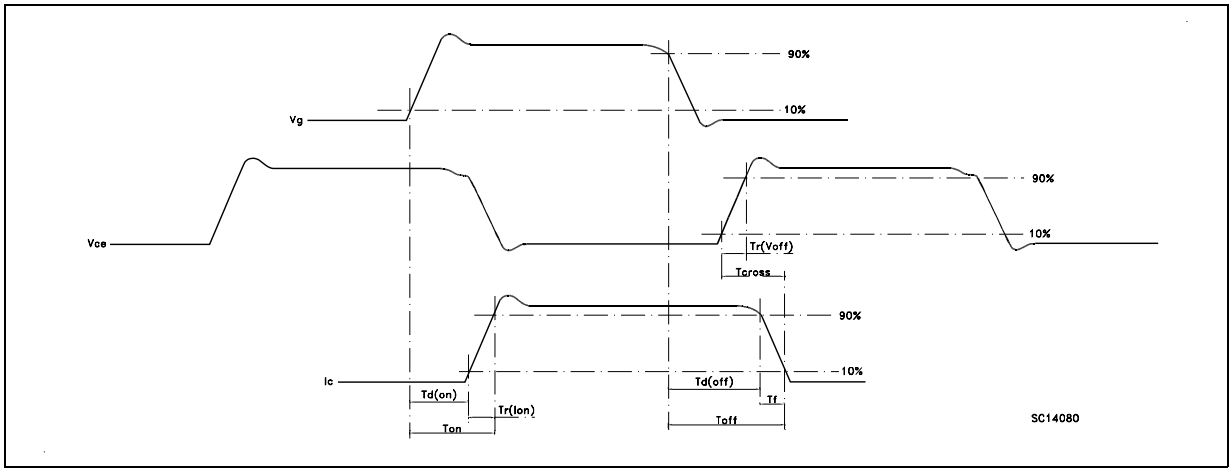
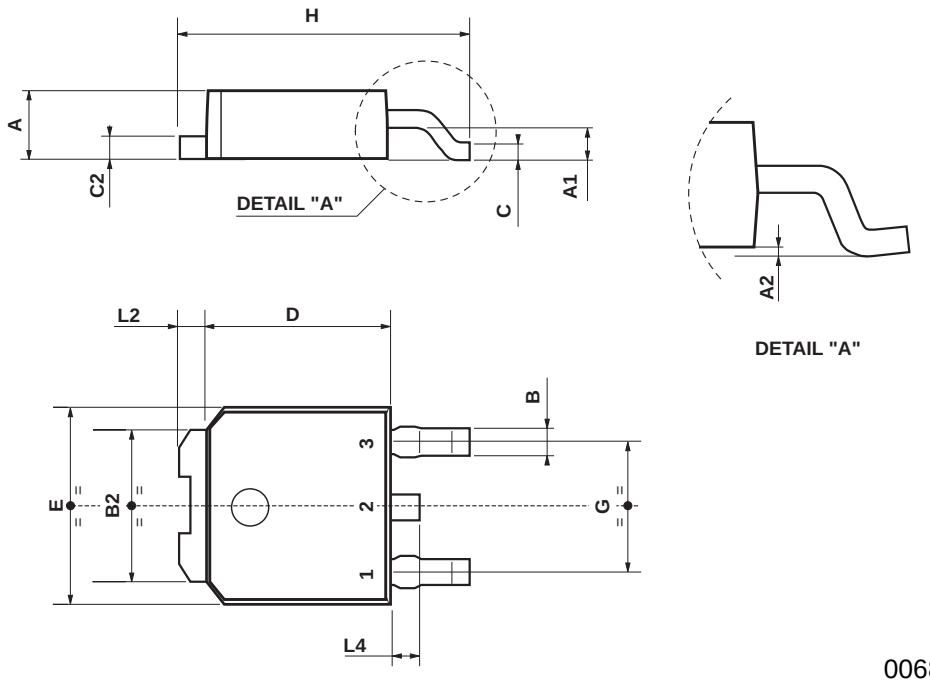


Fig. 3: Switching Waveforms



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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